



30N06

Power MOSFET

30A, 60V N-CHANNEL POWER MOSFET

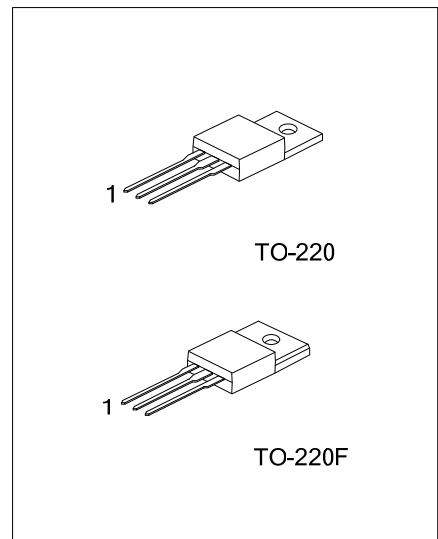
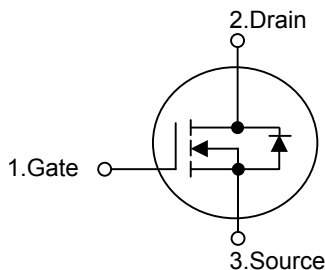
DESCRIPTION

The UTC 30N06 is a low voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and excellent avalanche characteristics. This power MOSFET is usually used at automotive applications in power supplies, high efficient DC to DC converters and battery operated products.

FEATURES

- * $V_{DS} = 60V$
- * $I_D = 30A$
- * $R_{DS(ON)} = 40m\Omega @ V_{GS} = 10V$
- * Ultra low gate charge (typical 20 nC)
- * Low reverse transfer Capacitance ($C_{RSS} =$ typical 80 pF)
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability

SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
30N06L-TA3-T	30N06G-TA3-T	TO-220	G	D	S	Tube
30N06L-TF3-T	30N06G-TF3-T	TO-220F	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>30N06L-TA3-T</p> <p>(1)Packing Type (2)Package Type (3)Lead Free</p>	<p>(1) T: Tube (2) TA3: TO-220, TF3: TO-220F (3) G: Halogen Free, L: Lead Free</p>
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■ ABSOLUTE MAXIMUM RATINGS($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Gate to Source Voltage		V_{GSS}	± 20	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	30	A
	$T_C = 100^\circ\text{C}$		21.3	A
Pulsed Drain Current (Note 2)		I_{DM}	120	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	300	mJ
	Repetitive (Note 2)	E_{AR}	8	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	7.5	V/ns
Power Dissipation	TO-220	P_D	79	W
	TO-220F		45	W/ $^\circ\text{C}$
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operation Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repeativity rating: pulse width limited by junction temperature

3. $L=0.66\text{mH}$, $I_{AS}=30\text{A}$, $V_{DD}=25\text{V}$, $R_G=20\Omega$, Starting $T_J=25^\circ\text{C}$

4. $I_{SD}\leq 50\text{A}$, $di/dt\leq 300\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$

■ THERMAL DATA

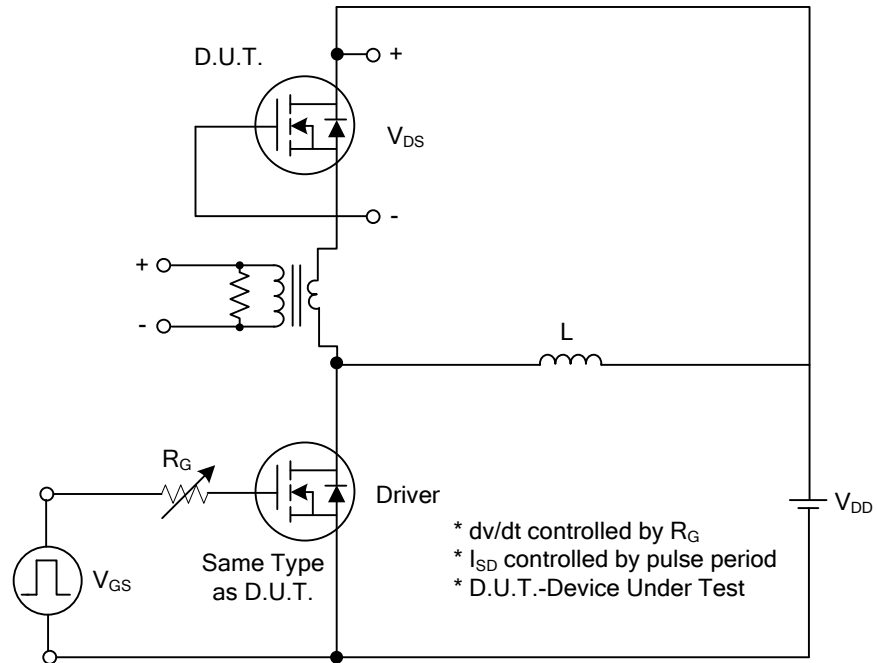
PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient		θ_{JA}	62	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220	θ_{JC}	1.9	$^\circ\text{C}/\text{W}$
	TO-220F		2.7	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

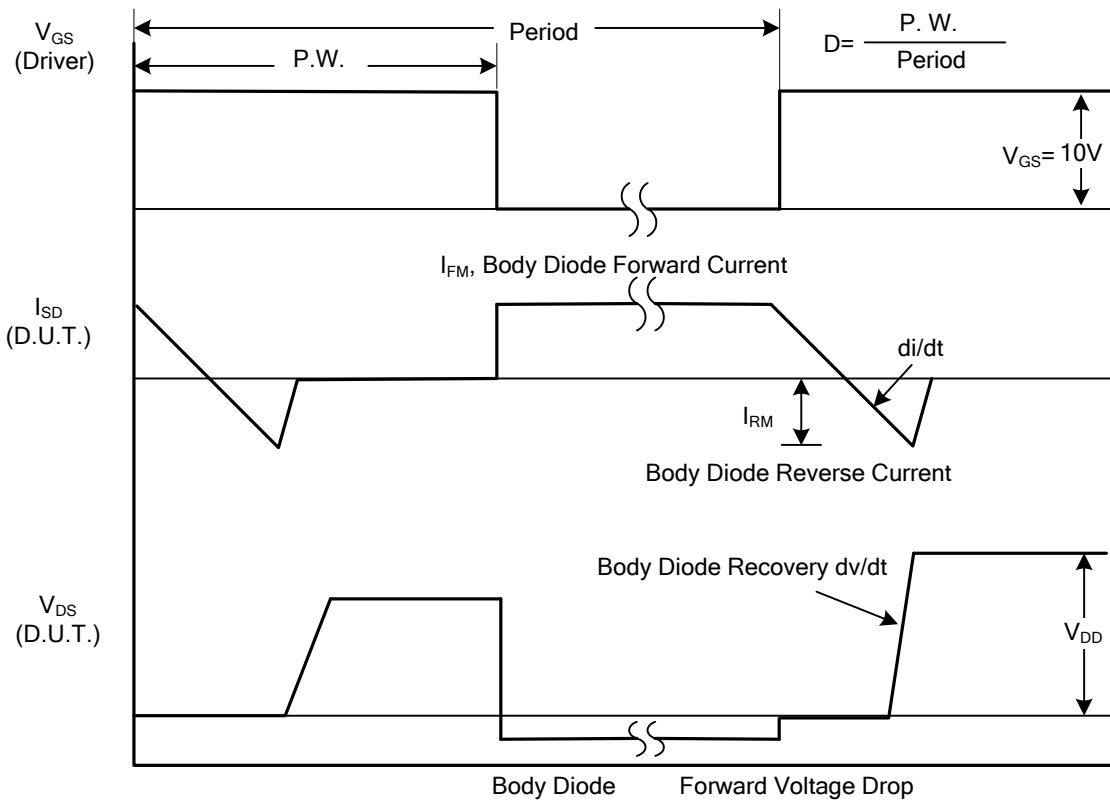
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	60			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}			100	nA
	Reverse				-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		0.06		$\text{V}/^\circ\text{C}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 15\text{ A}$		32	40	$\text{m}\Omega$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V},$ $f = 1\text{MHz}$		800		pF
Output Capacitance	C_{OSS}			300		pF
Reverse Transfer Capacitance	C_{RSS}			80		pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD} = 30\text{ V}, I_D = 15\text{ A}, V_{GS} = 10\text{ V}$ (Note 1, 2)		12		ns
Turn-On Rise Time	t_R			79		ns
Turn-Off Delay Time	$t_{D(OFF)}$			50		ns
Turn-Off Fall Time	t_F			52		ns
Total Gate Charge	Q_G	$V_{DS} = 60\text{ V}, V_{GS} = 10\text{ V},$ $I_D = 24\text{ A}$ (Note 1, 2)		20	30	nC
Gate-Source Charge	Q_{GS}			6		nC
Gate-Drain Charge	Q_{GD}			9		nC
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 30\text{ A}$			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				30	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				120	A
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, I_S = 30\text{ A},$ $di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 1)		40		ns
Reverse Recovery Charge	Q_{RR}			70		μC

- Notes: 1. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

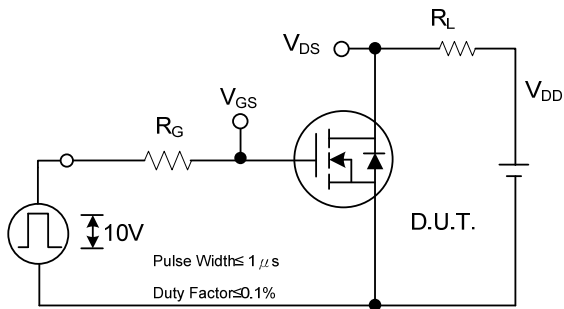


Peak Diode Recovery dv/dt Test Circuit

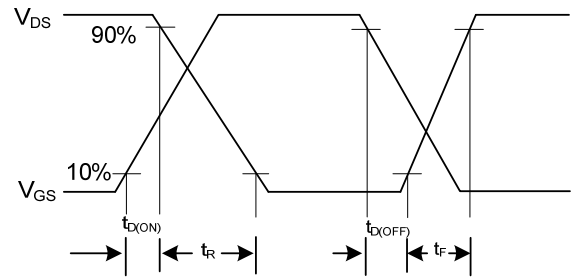


Peak Diode Recovery dv/dt Waveforms

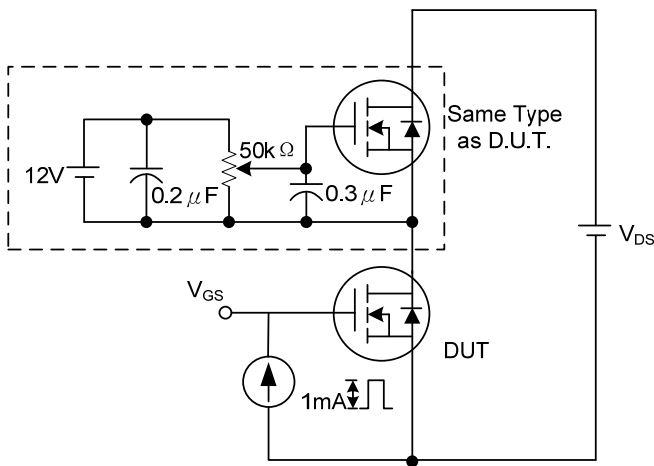
TEST CIRCUITS AND WAVEFORMS (Cont.)



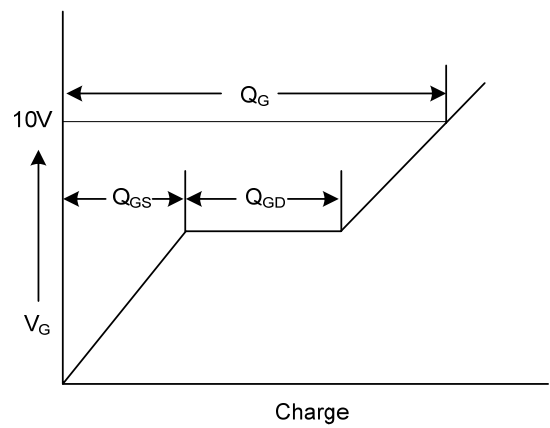
Switching Test Circuit



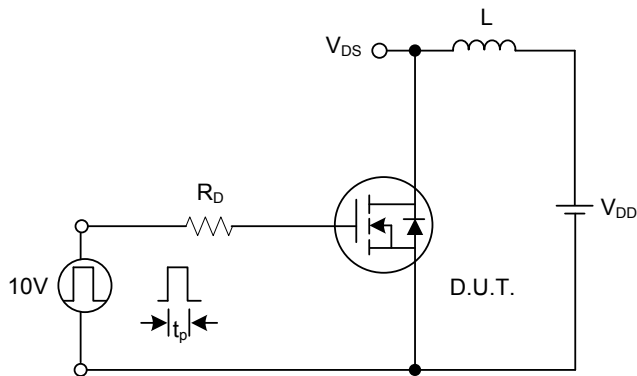
Switching Waveforms



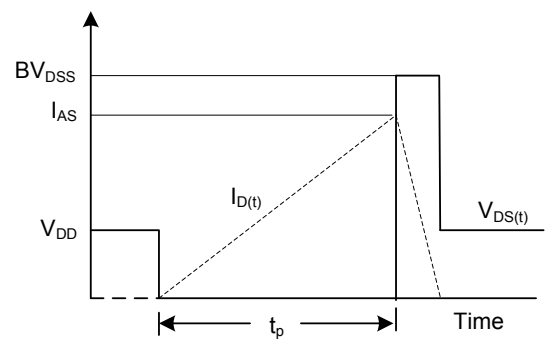
Gate Charge Test Circuit



Gate Charge Waveform

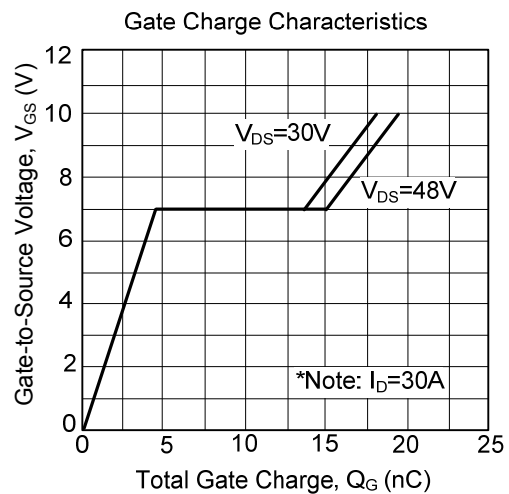
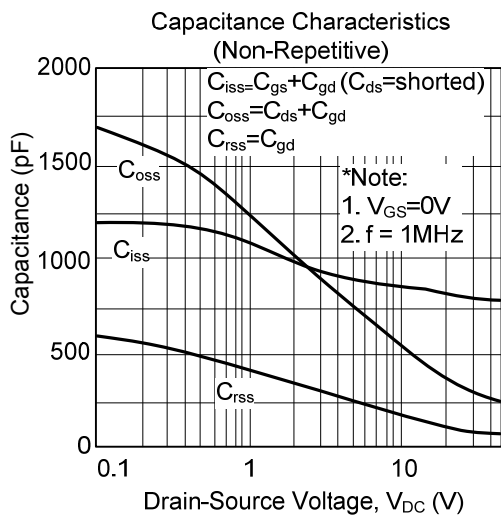
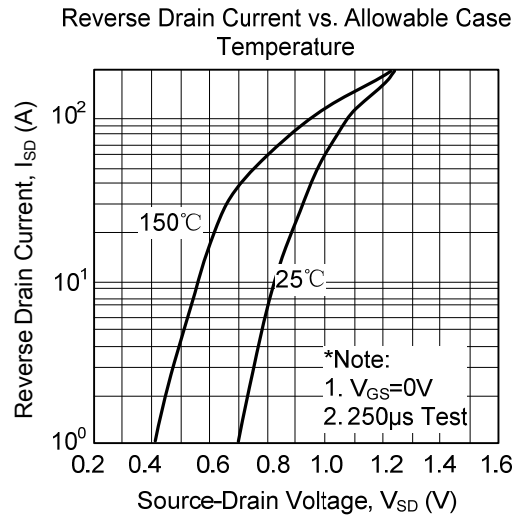
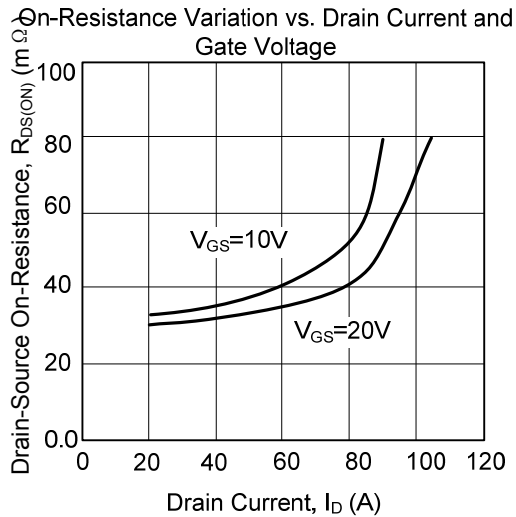
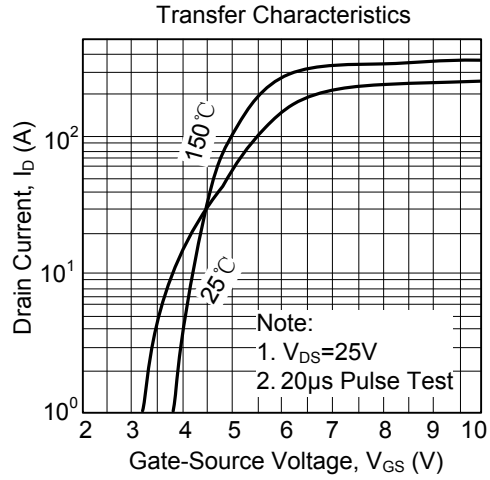
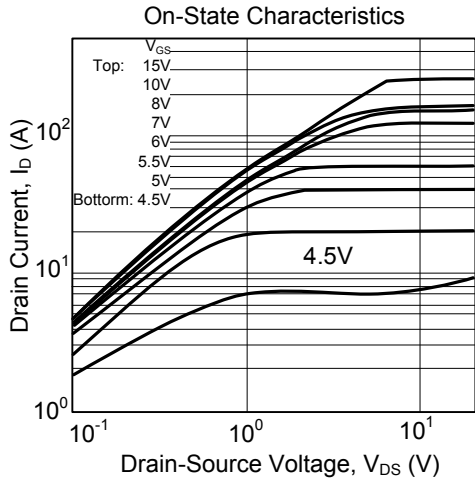


Unclamped Inductive Switching Test Circuit

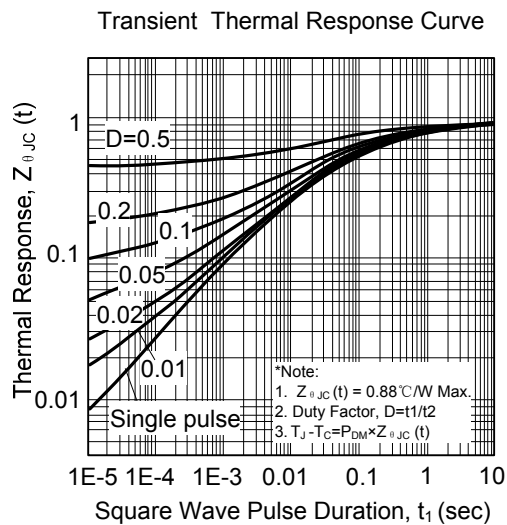
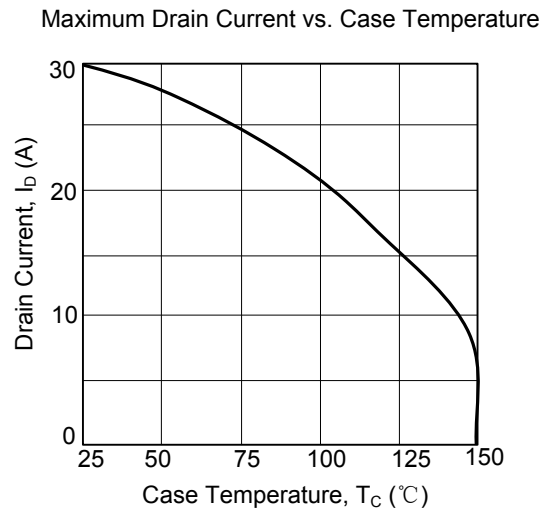
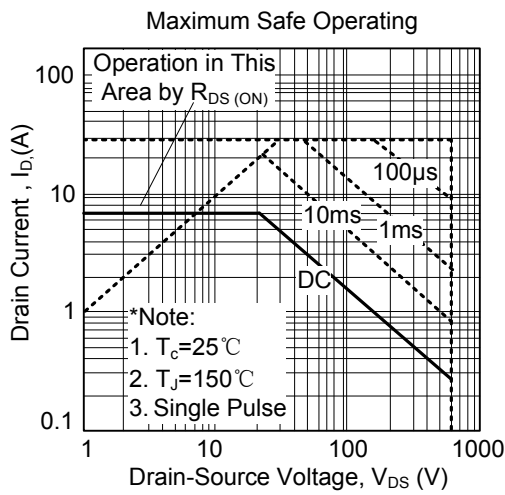
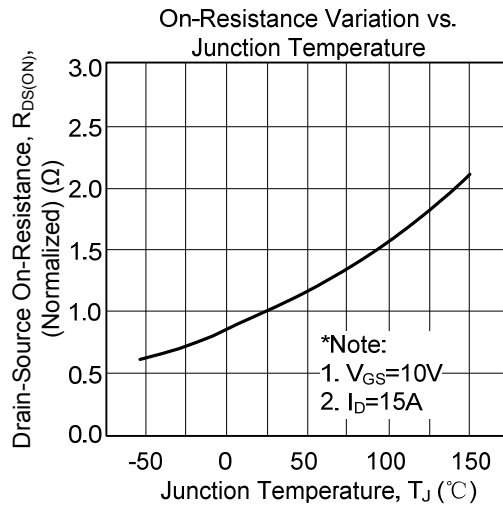
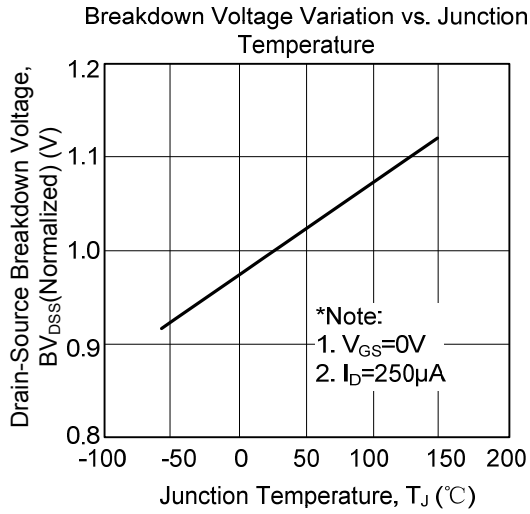


Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS(Cont.)



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